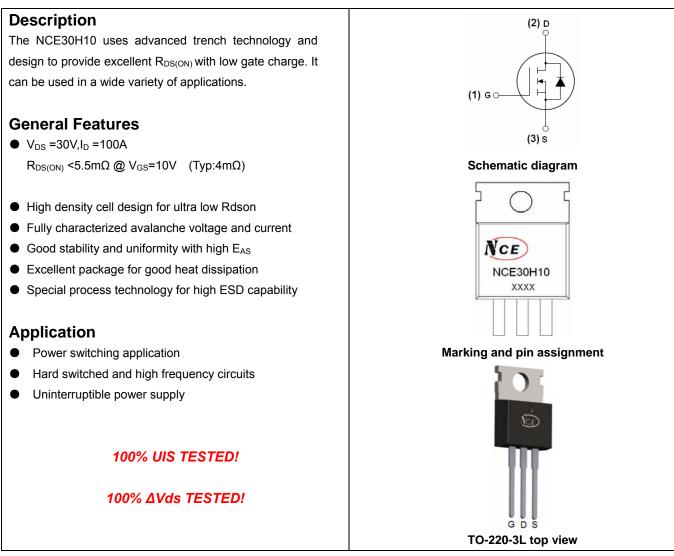


# NCE N-Channel Enhancement Mode Power MOSFET



#### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE30H10	NCE30H10	TO-220-3L	-	-	-

#### Absolute Maximum Ratings (T<sub>A</sub>=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	Ι <sub>D</sub>	100	A
Drain Current-Continuous(T <sub>C</sub> =100°C)	I <sub>D</sub> (100℃)	70	A
Pulsed Drain Current	I <sub>DM</sub>	400	A
Maximum Power Dissipation	PD	110	W
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	350	mJ
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 175	°C





#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>θJC</sub>	1.36	°C/W
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#### Electrical Characteristics (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·	·	•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)	·	·	•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	1	1.6	3	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	4.0	5.5	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =10V,I <sub>D</sub> =20A	50	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C <sub>lss</sub>			3300		PF
Output Capacitance	C <sub>oss</sub>			356		PF
Reverse Transfer Capacitance	C <sub>rss</sub>			308		PF
Switching Characteristics (Note 4)	·	·	•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	11	-	nS
Turn-on Rise Time	tr	$V_{DS}=25V, V_{GS}=0V,$ F=1.0MHz $V_{DD}=15V, I_{D}=30A$ $V_{GS}=4.5V, R_{GEN}=1.8\Omega$	-	160	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =4.5V, $R_{GEN}$ =1.8 $\Omega$	-	25	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	60	-	nS
Total Gate Charge	Qg			70		nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =15V,I <sub>D</sub> =30A, V <sub>GS</sub> =10V		8.8		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V		16.3		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =30A	-	-	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>	-	-	-	100	Α
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 30A	-	56	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	110	-	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negl	igible (turi	n-on is do	minated b	y LS+LD)

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

**2.** Surface Mounted on FR4 Board, t  $\leq$  10 sec.

**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

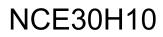
4. Guaranteed by design, not subject to production

5. EAS condition: Tj=25  $^\circ \!\! \mathbb{C}$  ,V\_{DD}=15V,V\_G=10V,L=0.5mH,Rg=25\Omega



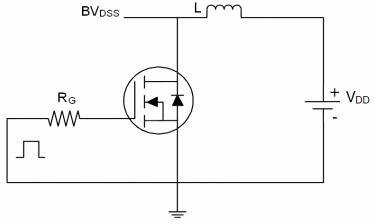
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Pb Free Product

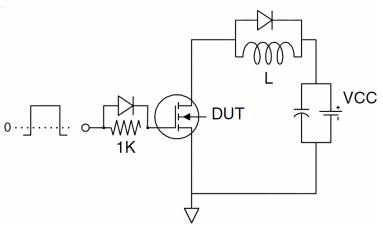


### Test circuit

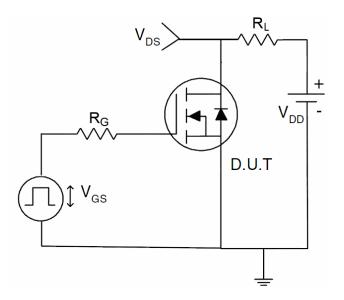
1) E<sub>AS</sub> test Circuits



#### 2) Gate charge test Circuit:



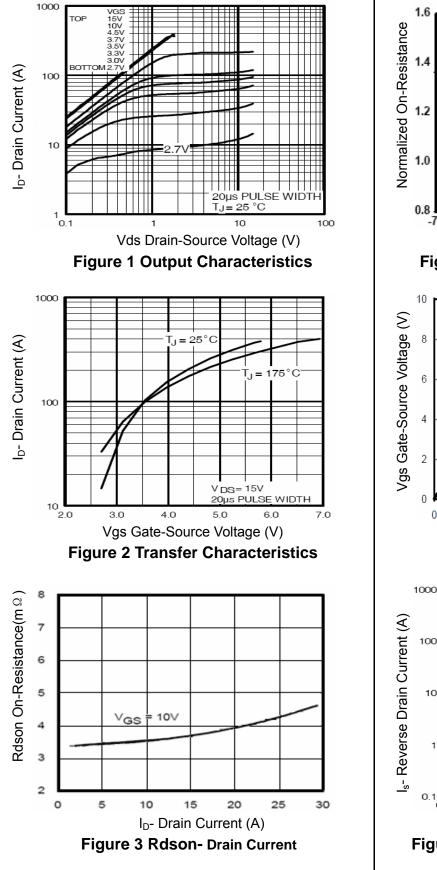
3) Switch Time Test Circuit:

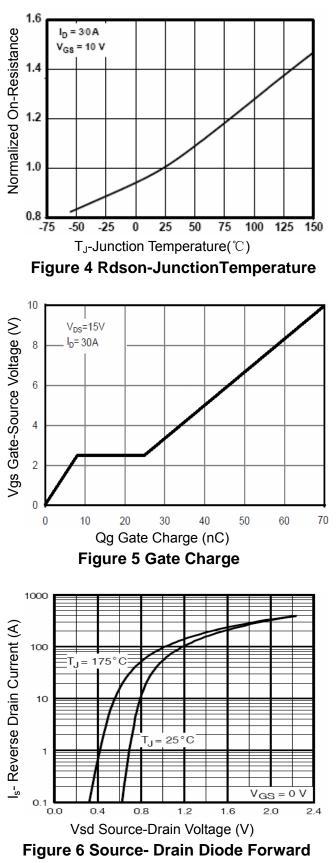






## **Typical Electrical and Thermal Characteristics (Curves)**







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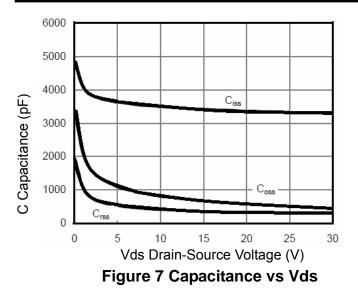
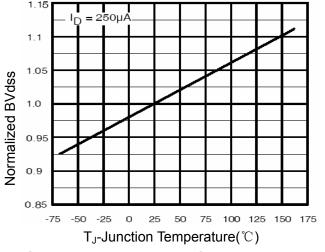


Figure 8 Safe Operation Area



**Pb Free Product** 

NCE30H10

Figure 9 BV<sub>DSS</sub> vs Junction Temperature

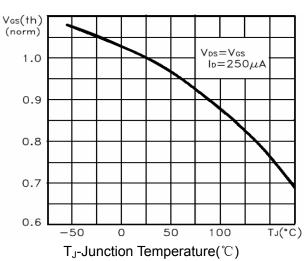
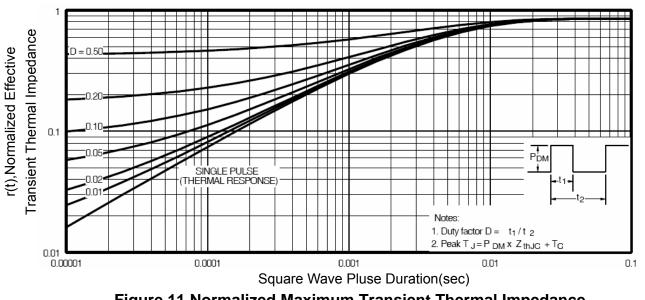
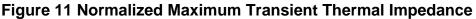


Figure 10 V<sub>GS(th)</sub> vs Junction Temperature





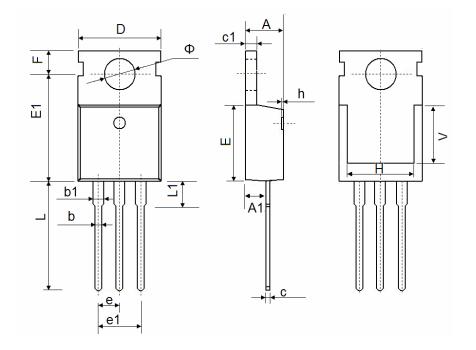


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# NCE30H10

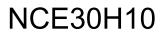
# **TO-220-3L Package Information**



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295	REF.	
Φ	3.400	3.800	0.134	0.150	







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